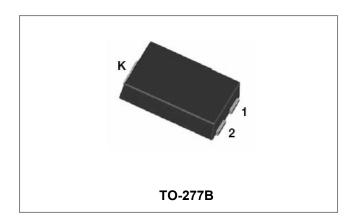






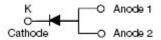
ST1545S SCHOTTKY RECTIFIER



Features

- 150°C T_J operation
- Center tap configuration
- Low forward voltage drop
- High purity, high temperature epoxy encapsulation for enhanced mechanical strength and moisture resistance
- High frequency operation
- Guard ring for enhanced ruggedness and long term reliability
- "-A" is an AEC-Q101 qualified device
- This is a Pb Free Device
- All SMC parts are traceable to the wafer lot
- Additional testing can be offered upon request

Circuit Diagram



Applications

- Switching power supply
- Converters
- Free-Wheeling diodes
- Reverse battery protection

Maximum Ratings:

Characteristics	Symbol	Condition	Max.	Units
Peak Repetitive Reverse Voltage	V_{RRM}	-		
Working Peak Reverse Voltage	V_{RWM}		45	V
DC Blocking Voltage	V_R			
Average Rectified Forward Current	I _{F (AV)}	50% duty cycle @T _L =125°C, rectangular wave form	15	Α
Peak One Cycle Non-Repetitive Surge Current	I _{FSM}	8.3ms, Half Sine pulse, T _c = 25 °C	200	Α

Electrical Characteristics:

Characteristics	Symbol	Condition	Тур.	Max.	Units
Forward Voltage Drop*		@ 5A, Pulse, T _J = 25 °C	0.38	0.50	
	V_{F1}	@ 7.5A, Pulse, T _J = 25 °C	0.40	0.52	V
		@ 15A, Pulse, T _J = 25 °C	0.46	0.58	
		@ 5A, Pulse, T _J = 125 °C	0.25	0.39	
	V_{F2}	@ 7.5A, Pulse, T _J = 125 °C	0.28	0.42	V
		@ 15A, Pulse, T _J = 125 °C	0.37	0.51	
Reverse Current*	I _{R1}	@V _R = rated V _R , T _J = 25 °C	0.2	1.5	mA
	I_{R2}	@V _R = rated V _R , T _J = 125 °C	110	150	mA
Junction Capacitance	Ст	$@V_R = 5V, T_C = 25 °C$ $f_{SIG} = 1MHz$	868	_	pF

^{*} Pulse width < 300 μ s, duty cycle < 2%

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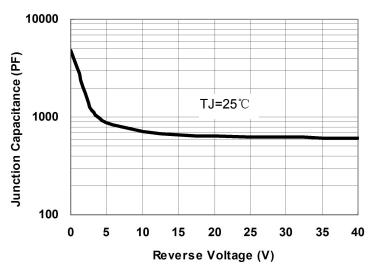


Thermal-Mechanical Specifications:

Characteristics	Symbol	Condition	Specification	Units
Junction Temperature	TJ	-	-55 to +150	°C
Storage Temperature	T _{stg}	-	-55 to +150	°C
Typical Thermal Resistance Junction to Ambient (NOTE1)	$R_{ heta JA}$	DC operation	75	°C/W
Typical Thermal Resistance Junction to Lead (NOTE1)	R _θ JL	DC operation	4	°C/W
Approximate Weight	wt	-	0.08	g

NOTE: 1. Units mounted on P.C.B., 0.5×0.5 " (30 x 30mm) copper pads.

Ratings and Characteristics Curves



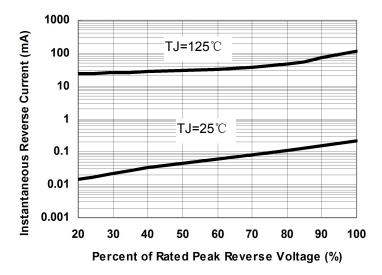


Fig.1-Typical Junction Capacitance

Fig.2-Typical Reverse Characteristics

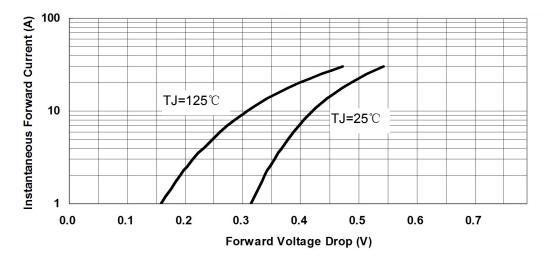


Fig.3-Typical Instantaneous Forward Voltage Characteristics

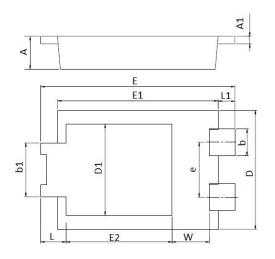
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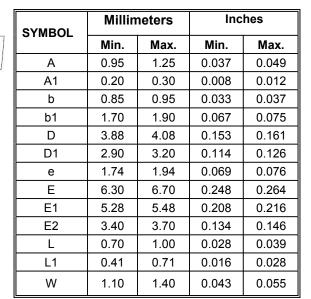




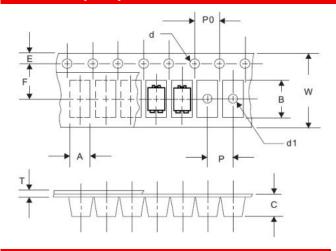


Mechanical Dimensions TO-277B





Carrier Tape Specification TO-277B



SYMBOL	Millimeters		
STWIBOL	Min.	Max.	
Α	4.28	4.48	
В	6.80	7.10	
С	1.30	1.50	
d	1.40	1.60	
d1	-	1.50	
E	1.65	1.85	
F	5.40	5.60	
Р	7.90	8.10	
P0	3.90	4.10	
T	0.24	0.44	
W	11.70	12.30	

Ordering Information

Device	Package	Shipping		
ST1545S	TO-277B(Pb-Free)	5000pcs/ reel		

For information on tape and reel specifications, including part orientation and tape sizes, please refer to our tape and reel packaging specification.

Marking Diagram





ST 15 45 S -A YY WW L

Where XXXXX is YYWWL

ST = Device Type 15 = Forward Current (15A) 45 = Reverse Voltage (45V) S = Package type

S = Package type
-A = AEC-Q101
YY = Year
WW = Week
L = Lot Number

Cautions: Molding resin

Epoxy resin UL:94V-0

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